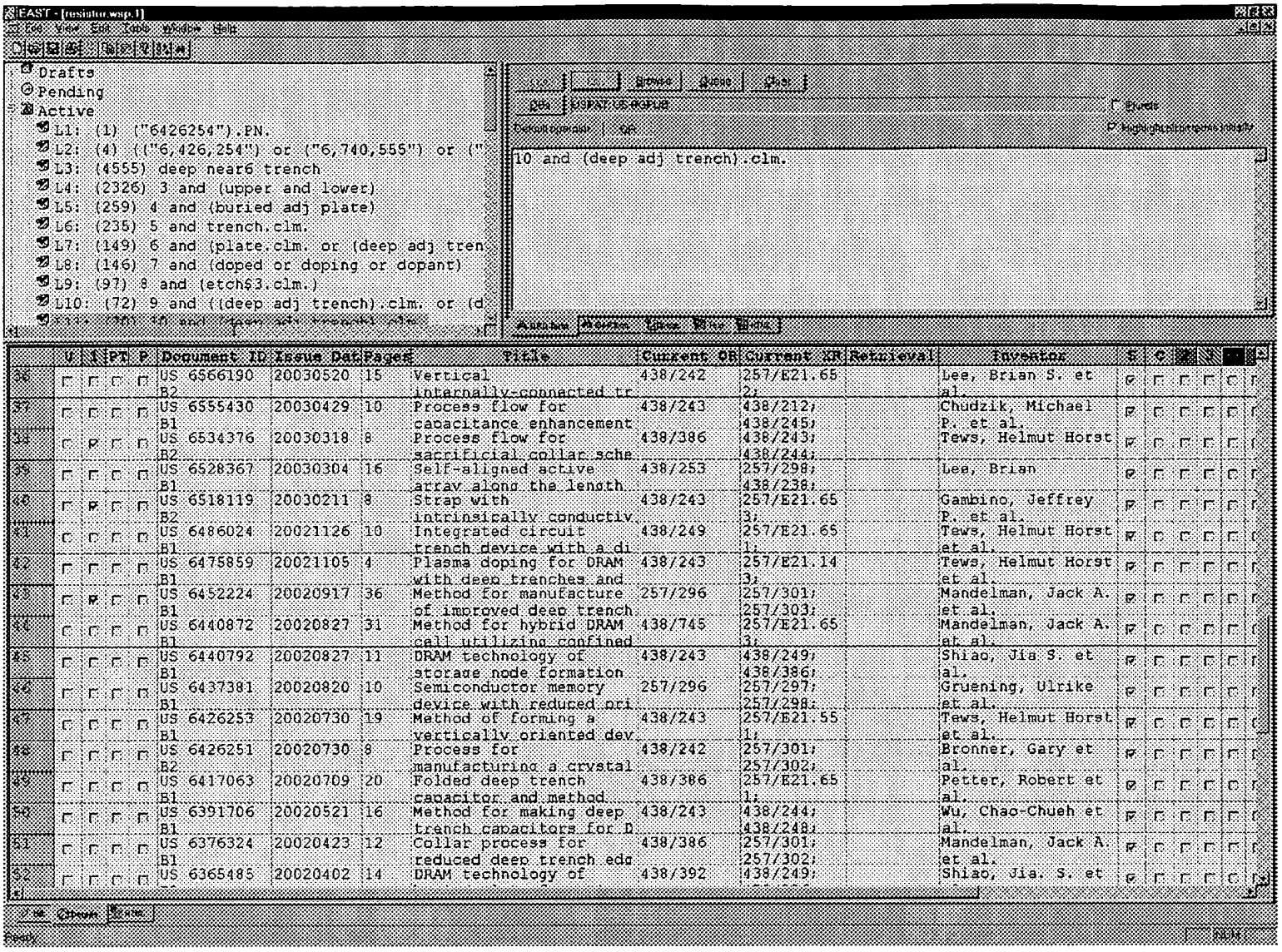

	U	1	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C
36					US 6566190 B2	20030520	15	Vertical internally-connected tr	438/242	257/E21.65 2;		Lee, Brian S. et al.		
37					US 6555430 B1	20030429	10	Process flow for capacitance enhancement	438/243	438/212; 438/245;		Chudzik, Michael P. et al.		
38					US 6534376 B2	20030318	8	Process flow for sacrificial collar sche	438/386	438/243; 438/244;		Tews, Helmut Horst		
39					US 6528367 B1	20030304	16	Self-aligned active array along the length	438/253	257/298; 438/238;		Lee, Brian		
40					US 6518119 B2	20030211	8	Strap with intrinsically conductiv	438/243	257/E21.65 3;		Gambino, Jeffrey P. et al.		
41					US 6486024 B1	20021126	10	Integrated circuit trench device with a di	438/249	257/E21.65 1;		Tews, Helmut Horst et al.		
42					US 6475859 B1	20021105	4	Plasma doping for DRAM with deep trenches and	438/243	257/E21.14 3;		Tews, Helmut Horst et al.		
43					US 6452224 B1	20020917	36	Method for manufacture of improved deep trench	257/296	257/301; 257/303;		Mandelman, Jack A. et al.		
44					US 6440872 B1	20020827	31	Method for hybrid DRAM cell utilizing confined	438/745	257/E21.65 3;		Mandelman, Jack A. et al.		
45					US 6440792 B1	20020827	11	DRAM technology of storage node formation	438/243	438/249; 438/386;		Shiao, Jia S. et al.		
46					US 6437381 B1	20020820	10	Semiconductor memory device with reduced pri	257/296	257/297; 257/298;		Gruening, Ulrike et al.		
47					US 6426253 B1	20020730	19	Method of forming a vertically oriented dev	438/243	257/E21.55 1;		Tews, Helmut Horst et al.		
48					US 6426251 B2	20020730	9	Process for manufacturing a crystal	438/242	257/301; 257/302;		Bronner, Gary et al.		
49					US 6417063 B1	20020709	20	Folded deep trench capacitor and method	438/386	257/E21.65 1;		Petter, Robert et al.		
50					US 6391706 B1	20020521	16	Method for making deep trench capacitors for D	438/243	438/244; 438/248;		Wu, Chao-Chueh et al.		
51					US 6376324 B1	20020423	12	Collar process for reduced deep trench edg	438/386	257/301; 257/302;		Mandelman, Jack A. et al.		
52					US 6365485	20020402	14	DRAM technology of	438/392	438/249;		Shiao, Jia. S. et		